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Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	240MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, MMC/SD, QSPI, SCI, SPI, SSI, UART/USART, USB
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	126
Program Memory Size	3MB (3M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	640K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 3.6V
Data Converters	A/D 21x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LFQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r7fs7g27g3a01cfc-aa0

1. Overview

The S7G2 MCU integrates multiple series of software- and pin-compatible ARM®-based 32-bit MCUs that share the same set of Renesas peripherals to facilitate design scalability and efficient platform-based product development.

The MCU provides a high-performance ARM Cortex®-M4 core running up to 240 MHz with the following features:

- Up to 4-MB code flash memory
- 640-KB SRAM
- Graphics LCD Controller (GLCDC)
- 2D Drawing Engine (DRW)
- Capacitive Touch Sensing Unit (CTSU)
- Ethernet MAC Controller (ETHERC) with IEEE 1588 PTP, USBFS, USBHS, SD/MMC Host Interface
- Quad Serial Peripheral Interface (QSPI)
- Security and safety features
- Analog peripherals.

1.1 Function Outline

Table 1.1 ARM core

Feature	Functional description
ARM Cortex-M4	<ul style="list-style-type: none"> • Maximum operating frequency: up to 240 MHz • ARM Cortex-M4 core: <ul style="list-style-type: none"> - Revision: r0p1-01rel0 - ARMv7E-M architecture profile - Single precision floating point unit compliant with the ANSI/IEEE Std 754-2008 • ARM Memory Protection Unit (MPU): <ul style="list-style-type: none"> - ARMv7 Protected Memory System Architecture - 8 protect regions • SysTick timer: <ul style="list-style-type: none"> - Driven by LOCO clock

Table 1.2 Memory

Feature	Functional description
Code flash memory	Maximum 4 MB of code flash memory. See section 54, Flash Memory in User's Manual.
Data flash memory	64 KB of data flash memory. See section 54, Flash Memory in User's Manual.
Memory Mirror Function (MMF)	The MMF can be configured to mirror the wanted application image load address in code flash memory to the application image link address in the 23-bit unused memory space (memory mirror space addresses). Your application code is developed and linked to run from this MMF destination address. The application code does not need to know the load location where it is stored in code flash memory. See section 5, Memory Mirror Function (MMF) in User's Manual.
SRAM	On-chip high-speed SRAM providing either parity-bit or double-bit error detection (DED). The first 32 KB of SRAM0 is subject to DED. Parity check is performed for other areas. See section 52, SRAM in User's Manual.
Standby SRAM	On-chip SRAM that can retain data in Deep Software Standby mode. See section 53, Standby SRAM in User's Manual.

Table 1.3 System (1/2)

Feature	Functional description
Operating modes	Two operating modes: <ul style="list-style-type: none"> - Single-chip mode - SCI or USB boot mode. See section 3, Operating Modes in User's Manual.

Table 1.9 Communication interfaces (1/2)

Feature	Functional description
Serial Communications Interface (SCI)	<p>The SCI is configurable to five asynchronous and synchronous serial interfaces:</p> <ul style="list-style-type: none"> • Asynchronous interfaces (UART and Asynchronous Communications Interface Adapter (ACIA)) • 8-bit clock synchronous interface • Simple IIC (master-only) • Simple SPI • Smart card interface. <p>The smart card interface complies with the ISO/IEC 7816-3 standard for electronic signals and transmission protocol.</p> <p>Each SCI has FIFO buffers to enable continuous and full-duplex communication, and the data transfer speed can be configured independently using an on-chip baud rate generator. See section 34, Serial Communications Interface (SCI) in User's Manual.</p>
IrDA Interface (IrDA)	<p>The IrDA interface sends and receives IrDA data communication waveforms in cooperation with the SCI1 based on the IrDA (Infrared Data Association) standard 1.0. See section 35, IrDA Interface in User's Manual.</p>
I ² C Bus Interface (IIC)	<p>The three-channel IIC conforms with and provides a subset of the NXP I²C bus (Inter-Integrated Circuit bus) interface functions. See section 36, I²C Bus Interface (IIC) in User's Manual.</p>
Serial Peripheral Interface (SPI)	<p>Two independent SPI channels are capable of high-speed, full-duplex synchronous serial communications with multiple processors and peripheral devices. See section 38, Serial Peripheral Interface (SPI) in User's Manual.</p>
Serial Sound Interface (SSI)	<p>The SSI peripheral provides functionality to interface with digital audio devices for transmitting PCM audio data over a serial bus with the MCU. The SSI supports an audio clock frequency of up to 50 MHz, and can be operated as a slave or master receiver, transmitter, or transceiver to suit various applications. The SSI includes 8-stage FIFO buffers in the receiver and transmitter, and supports interrupts and DMA-driven data reception and transmission. See section 41, Serial Sound Interface (SSI) in User's Manual.</p>
Quad Serial Peripheral Interface (QSPI)	<p>The QSPI is a memory controller for connecting a serial ROM (nonvolatile memory such as a serial flash memory, serial EEPROM, or serial FeRAM) that has an SPI-compatible interface. See section 39, Quad Serial Peripheral Interface (QSPI) in User's Manual.</p>
Controller Area Network (CAN) Module	<p>The CAN module provides functionality to receive and transmit data using a message-based protocol between multiple slaves and masters in electromagnetically-noisy applications. The CAN module complies with the ISO 11898-1 (CAN 2.0A/CAN 2.0B) standard and supports up to 32 mailboxes, which can be configured for transmission or reception in normal mailbox and FIFO modes. Both standard (11-bit) and extended (29-bit) messaging formats are supported. See section 37, Controller Area Network (CAN) Module in User's Manual.</p>
USB 2.0 Full-Speed Module (USBFS)	<p>Full-Speed USB controller that can operate as a host controller or device controller. The module supports full-speed and low-speed (host controller only) transfer as defined in Universal Serial Bus Specification 2.0. The module has an internal USB transceiver and supports all of the transfer types defined in Universal Serial Bus Specification 2.0. The USB has buffer memory for data transfer, providing a maximum of 10 pipes. Pipes 1 to 9 can be assigned any endpoint number based on the peripheral devices used for communication or based on your system. See section 32, USB 2.0 Full-Speed Module (USBFS) in User's Manual.</p>
USB 2.0 High-Speed Module (USBHS)	<p>High-Speed USB controller that can operate as a host controller or a device controller. As a host controller, the USBHS supports high-speed transfer, full-speed transfer, and low-speed transfer as defined in Universal Serial Bus Specification 2.0. As a device controller, the USBHS supports high-speed transfer and full-speed transfer as defined in Universal Serial Bus Specification 2.0. The USBHS has an internal USB transceiver and supports all of the transfer types defined in Universal Serial Bus Specification 2.0. The USBHS has FIFO buffers for data transfer, providing a maximum of 10 pipes. Any endpoint number can be assigned to pipes 1 to 9, based on the peripheral devices or your system for communication. See section 33, USB 2.0 High-Speed Module (USBHS) in User's Manual.</p>

Table 1.11 Human machine interfaces (2/2)

Feature	Functional description
Capacitive Touch Sensing Unit (CTSU)	The CTSU measures the electrostatic capacitance of the touch sensor. Changes in the electrostatic capacitance are determined by the software, which enables the CTSU to detect whether a finger is in contact with the touch sensor. The electrode surface of the touch sensor is usually enclosed with an electrical conductor so that fingers do not come into direct contact with the electrodes. See section 50, Capacitive Touch Sensing Unit (CTSU) in User's Manual.

Table 1.12 Graphics

Feature	Functional description
Graphics LCD Controller (GLCDC)	<p>The GLCDC provides multiple functions and supports various data formats and panels. Key GLCDC features include:</p> <ul style="list-style-type: none"> • GPX bus master function for accessing graphics data • Superimposition of three planes (single color background plane, graphic 1 plane, and graphic 2 plane) • Support for many types of 32- or 16-bit per pixel graphics data and 8-, 4-, or 1-bit LUT data format • Digital interface signal output supporting a video image size of WVGA or greater. <p>See section 57, Graphics LCD Controller (GLCDC) in User's Manual.</p>
2D Drawing Engine (DRW)	<p>The 2D Drawing Engine (DRW) provides flexible functions that can support almost any object geometry rather than being bound to only a few specific geometries such as lines, triangles, or circles. The edges of every object can be independently blurred or antialiased. Rasterization is executed at one pixel per clock on the bounding box of the object from left to right and top to bottom. The DRW can also raster from bottom to top to optimize the performance in certain cases. In addition, optimization methods are available to avoid rasterization of many empty pixels of the bounding box.</p> <p>The distances to the edges of the object are calculated by a set of edge equations for every pixel of the bounding box. These edge equations can be combined to describe the entire object.</p> <p>If a pixel is inside the object, it is selected for rendering. If it is outside it is discarded. If it is on the edge, an alpha value can be chosen proportional to the distance of the pixel to the nearest edge for antialiasing.</p> <p>Every pixel that is selected for rendering can be textured. The resulting aRGB quadruple can be modified by a general raster operation approach independently for each of the four channels. The aRGB quadruples can then be blended with one of the multiple blend modes of the DRW.</p> <p>The DRW provides two inputs (texture read and framebuffer read), and one output (framebuffer write).</p> <p>The internal color format is always aRGB (8888). The color formats from the inputs are converted to the internal format on read and a conversion back is made on write.</p> <p>See section 55, 2D Drawing Engine (DRW) in User's Manual.</p>
JPEG Codec (JPEG)	The JPEG Codec (JPEG) incorporates a JPEG codec that conforms to the JPEG baseline compression and decompression standard. This provides high-speed compression of image data and high-speed decoding of JPEG data. See section 56, JPEG Codec in User's Manual.
Parallel Data Capture Unit (PDC)	One PDC unit is provided for communicating with external I/O devices, including image sensors, and transferring parallel data such as an image output from the external I/O device through the DTC or DMAC to the on-chip SRAM and external address spaces (the CS and SDRAM areas). See section 44, Parallel Data Capture Unit (PDC) in User's Manual.

Table 1.13 Data processing (1/2)

Feature	Functional description
Cyclic Redundancy Check (CRC) calculator	The CRC calculator generates CRC codes to detect errors in the data. The bit order of CRC calculation results can be switched for LSB-first or MSB-first communication. Additionally, various CRC-generating polynomials are available. The snoop function allows monitoring reads from and writes to specific addresses. This function is useful in applications that require CRC code to be generated automatically in certain events, such as monitoring writes to the serial transmit buffer and reads from the serial receive buffer. See section 40, Cyclic Redundancy Check (CRC) Calculator in User's Manual.
Data Operation Circuit (DOC)	The DOC compares, adds, and subtracts 16-bit data. See section 51, Data Operation Circuit (DOC) in User's Manual.

1.2 Block Diagram

Figure 1.1 shows the block diagram of the MCU superset. Some individual devices within the group have a subset of the features.

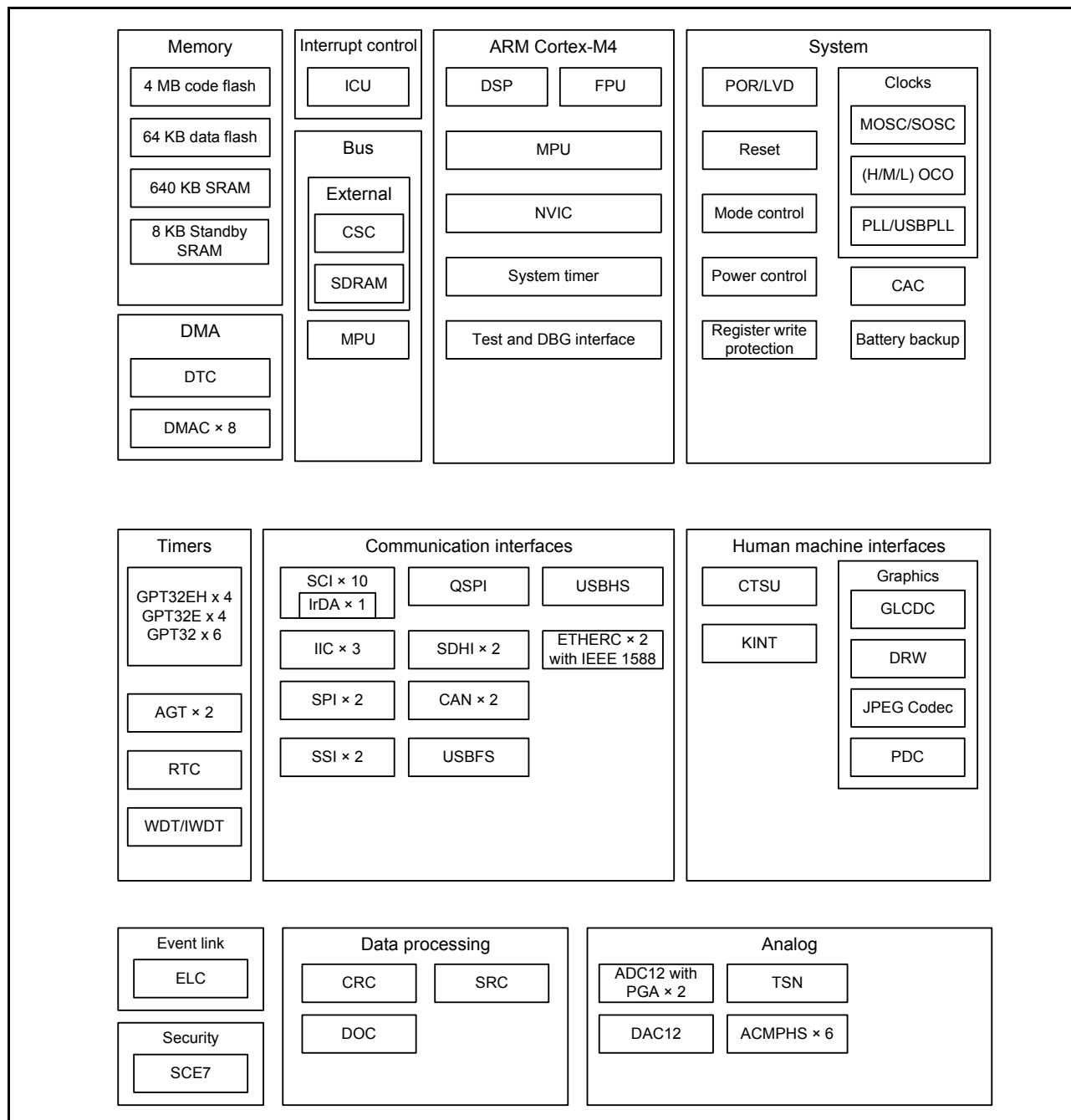


Figure 1.1 Block diagram

Table 1.16 Pin functions (2/5)

Function	Signal	I/O	Description
SDRAM interface	CKE	Output	SDRAM clock enable signal.
	SDCS	Output	SDRAM chip select signal, active LOW.
	RAS	Output	SDRAM low address strobe signal, active LOW.
	CAS	Output	SDRAM column address strobe signal, active LOW.
	WE	Output	SDRAM write enable signal, active LOW.
	DQM0	Output	SDRAM I/O data mask enable signal for DQ07 to DQ00.
	DQM1	Output	SDRAM I/O data mask enable signal for DQ15 to DQ08.
	A00 to A15	Output	Address bus.
	DQ00 to DQ15	I/O	Data bus.
Interrupt	NMI	Input	Non-maskable interrupt request pin.
	IRQ0 to IRQ15	Input	Maskable interrupt request pins.
GPT	GTETRGA, GTETRGB, GTETRGC, GTETRGD	Input	External trigger input pins.
	GTIOC0A to GTIOC13A, GTIOC0B to GTIOC13B	I/O	Input capture, output compare, or PWM output pins.
	GTIU	Input	Hall sensor input pin U.
	GTIV	Input	Hall sensor input pin V.
	GTIW	Input	Hall sensor input pin W.
	GTOUUP	Output	Three-phase PWM output for BLDC motor control (positive U phase).
	GTOULO	Output	Three-phase PWM output for BLDC motor control (negative U phase).
	GTOVUP	Output	Three-phase PWM output for BLDC motor control (positive V phase).
	GTOVLO	Output	Three-phase PWM output for BLDC motor control (negative V phase).
	GTOWUP	Output	Three-phase PWM output for BLDC motor control (positive W phase).
	GTOWLO	Output	Three-phase PWM output for BLDC motor control (negative W phase).
AGT	AGTEE0, AGTEE1	Input	External event input enable signals.
	AGTIO0, AGTIO1	I/O	External event input and pulse output pins.
	AGTO0, AGTO1	Output	Pulse output pins.
	AGTOA0, AGTOA1	Output	Output compare match A output pins.
	AGTOB0, AGTOB1	Output	Output compare match B output pins.
RTC	RTCOUT	Output	Output pin for 1-Hz or 64-Hz clock.
	RTCIC0 to RTCIC2	Input	Time capture event input pins.
SCI	SCK0 to SCK9	I/O	Input/output pins for the clock (clock synchronous mode).
	RXD0 to RXD9	Input	Input pins for received data (asynchronous mode/clock synchronous mode).
	TXD0 to TXD9	Output	Output pins for transmitted data (asynchronous mode/clock synchronous mode).
	CTS0_RTS0 to CTS9_RTS9	I/O	Input/output pins for controlling the start of transmission and reception (asynchronous mode/clock synchronous mode), active LOW.
	SCL0 to SCL9	I/O	Input/output pins for the IIC clock (simple IIC).
	SDA0 to SDA9	I/O	Input/output pins for the IIC data (simple IIC).
	SCK0 to SCK9	I/O	Input/output pins for the clock (simple SPI).
	MISO0 to MISO9	I/O	Input/output pins for slave transmission of data (simple SPI).
	MOSI0 to MOSI9	I/O	Input/output pins for master transmission of data (simple SPI).
	SS0 to SS9	Input	Chip-select input pins (simple SPI), active LOW.
IIC	SCL0 to SCL2	I/O	Input/output pins for the clock.
	SDA0 to SDA2	I/O	Input/output pins for data.

Table 1.17 Pin list (9/12)

Pin number						Power, System, Clock, Debug,	I/O port	Extbus		Timers				Communication interfaces										Analog		HMI		GLCDC, PDC
BGA224	BGA176	LQFP176	LGA145	LQFP144	LQFP100			External bus	SDRAM	AGT	GPT	GPT	RTC	USBFS, CAN	SCI0,2,4,6,8 (30 MHz)	SCI1,3,5,7,9 (30 MHz)	IIC	SPI, QSPI	SSI	MII (25 MHz)	RMI (50 MHz)	USBHS	SDHI	ADC12	DAC12, ACMPHS	CTSU	Interrupt	
J5	-	-	-	-	-		PA0 3	-	-	-	-	-	-	-	-	RX D7_ B/ MIS O7_ B/ SC L7_ B	-	-	-	-	-	-	-	-	-	-	IRQ 9	-
H6	-	-	-	-	-		PA0 2	-	-	-	-	-	-	-	-	TX D7_ B/ MO SI7 B/ SD A7_ B	-	-	-	-	-	-	-	-	-	-	IRQ 10	-
J6	H2	113	-	-	-		PA0 1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LC D_ DA TA0 6_B
J7	H4	114	-	-	-		PA0 0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LC D_ DA TA0 5_B
K5	J4	115	-	-	-		P60 7	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LC D_ DA TA0 4_B
K6	J1	116	-	-	-		P60 6	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LC D_ DA TA0 3_B
K1	J2	117	H2	93	-		P60 5	D11	DQ 11	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
K2	J3	118	G4	94	-		P60 4	D12	DQ 12	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
K3	K3	119	H3	95	-		P60 3	D13	DQ 13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
L1	K1	120	J1	96	65		P60 2	EB CL K	SD CL K	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LC D_ DA TA0 4_A
L2	K2	121	J2	97	66	-	P60 1	WR /W R0	DQ M0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LC D_ DA TA0 3_A
L3	L1	122	H4	98	67	-	P60 0	RD	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LC D_ DA TA0 2_A
M2	K4	123	K2	99	-	VC C	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
M1	L4	124	K1	100	-	VS S	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
K4	L2	125	J3	101	68	-	P10 7	D07	DQ 07	-	-	GTI OC 8A_ A	-	-	CT S8_ RT S8_ A/ SS 8_A	-	-	-	-	-	-	-	-	-	-	-	KR 07	LC D_ DA TA0 1_A
L4	M1	126	K3	102	69	-	P10 6	D06	DQ 06	-	-	GTI OC 8B_ A	-	-	SC K8_ A	-	-	SS LA3 _A	-	-	-	-	-	-	-	-	KR 06	LC D_ DA TA0 0_A
M3	L3	127	J4	103	70	-	P10 5	D05	DQ 05	-	GT ET RG A_ C	-	-	-	TX D8_ A/ MO SI8 _A/ SD A8_ A	-	-	SS LA2 _A	-	-	-	-	-	-	-	-	IRQ 0/K R05	LC D_ TC ON 3_A
N3	M2	128	L3	104	71	-	P10 4	D04	DQ 04	-	GT ET RG B_ B	-	-	-	RX D8_ A/ MIS O8 _A/ SC L8_ A	-	-	SS LA1 _A	-	-	-	-	-	-	-	-	IRQ 1/K R04	LC D_ TC ON 2_A

2. Electrical Characteristics

Unless otherwise specified, the electrical characteristics of the MCU are defined under the following conditions:

$VCC = AVCC0 = VCC_USB = VBATT = 2.7$ to 3.6 V, $2.7 \leq VREFH0/VREFH \leq AVCC0$, $VCC_USBHS = AVCC_USBHS = 3.0$ to 3.6 V, $VSS = AVSS0 = VREFL0/VREFL = VSS_USB = VSS1_USBHS = VSS2_USBHS = PVSS_USBHS = AVSS_USBHS = 0$ V, $T_a = T_{opr}$

Figure 2.1 shows the timing conditions.

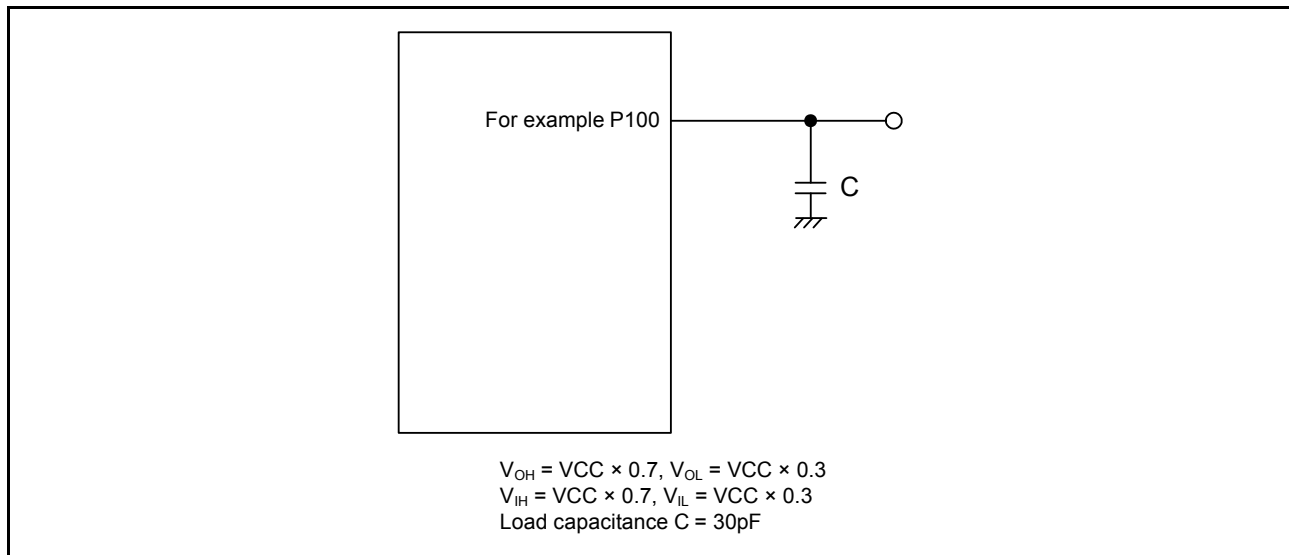


Figure 2.1 Input or output timing measurement conditions

The measurement conditions of timing specification in each peripherals are recommended for the best peripheral operation, however make sure to adjust driving abilities of each pins to meet your conditions.

2.1 Absolute Maximum Ratings

Table 2.1 Absolute maximum ratings

Item	Symbol	Value	Unit
Power supply voltage	VCC, VCC_USB *2	-0.3 to +4.6	V
VBATT power supply voltage	VBATT	-0.3 to +4.6	V
Input voltage (except for 5V-tolerant ports*1)	V_{in}	-0.3 to $VCC + 0.3$	V
Input voltage (5V-tolerant ports*1)	V_{in}	-0.3 to +5.8	V
Reference power supply voltage	$VREFH/VREFH0$	-0.3 to $VCC + 0.3$	V
Analog power supply voltage	AVCC0 *2	-0.3 to +4.6	V
USBHS power supply voltage	VCC_USBHS	-0.3 to +4.6	V
USBHS analog power supply voltage	AVCC_USBHS	-0.3 to +4.6	V
Switching regulator power supply voltage	VCC_DCDC	-0.3 to +4.6	V
Analog input voltage	V_{AN}	-0.3 to $AVCC0 + 0.3$	V
Operating temperature*3 *4	T_{opr}	-40 to +105	°C
Storage temperature	T_{stg}	-55 to +125	°C

Caution: Permanent damage to the MCU might result if absolute maximum ratings are exceeded.

Note 1. Ports P205, P206, P400, P401, P407 to P415, P511, P512, P708 to P713, and PB01 are 5V-tolerant.

Note 2. Connect AVCC0 and VCC_USB to VCC.

Note 3. See [section 2.2.1, Tj/Ta Definition](#).

Note 4. Contact a Renesas Electronics sales office for information on derating operation when $T_a = +85^\circ\text{C}$ to $+105^\circ\text{C}$.

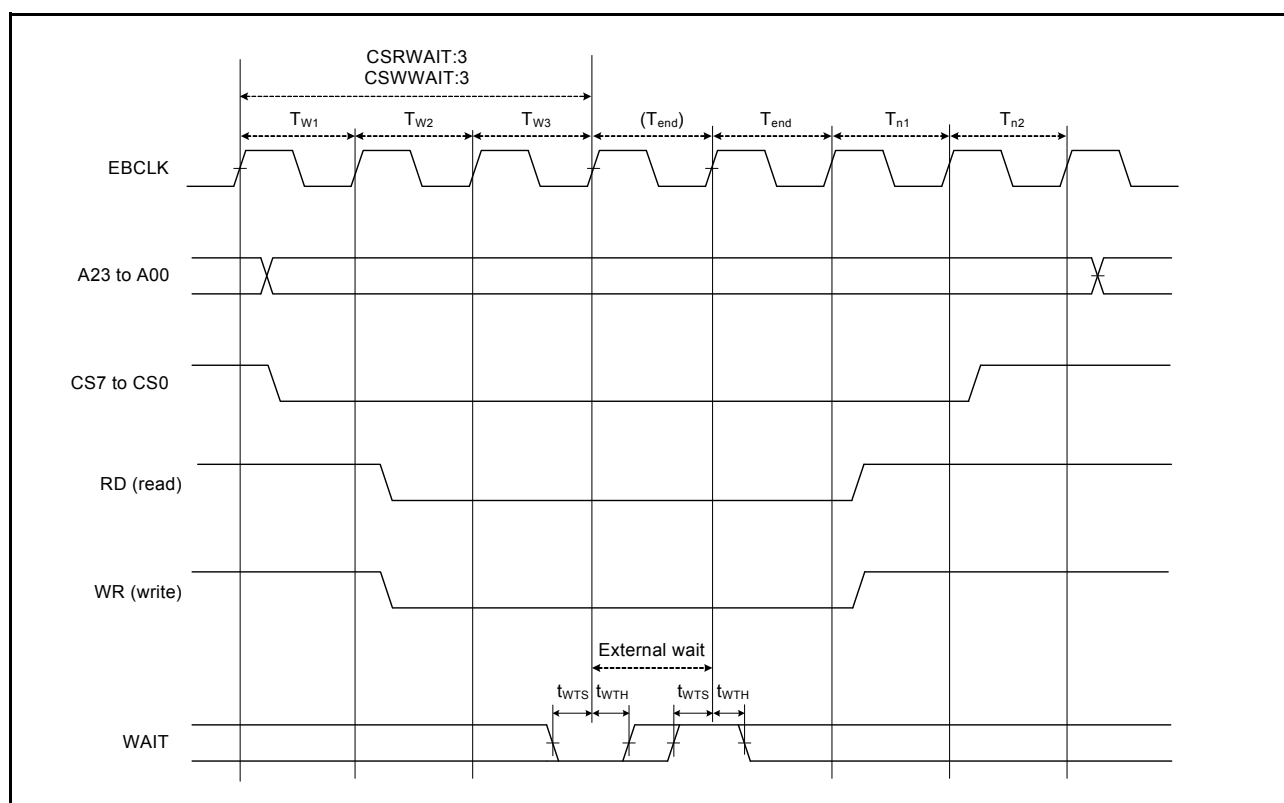
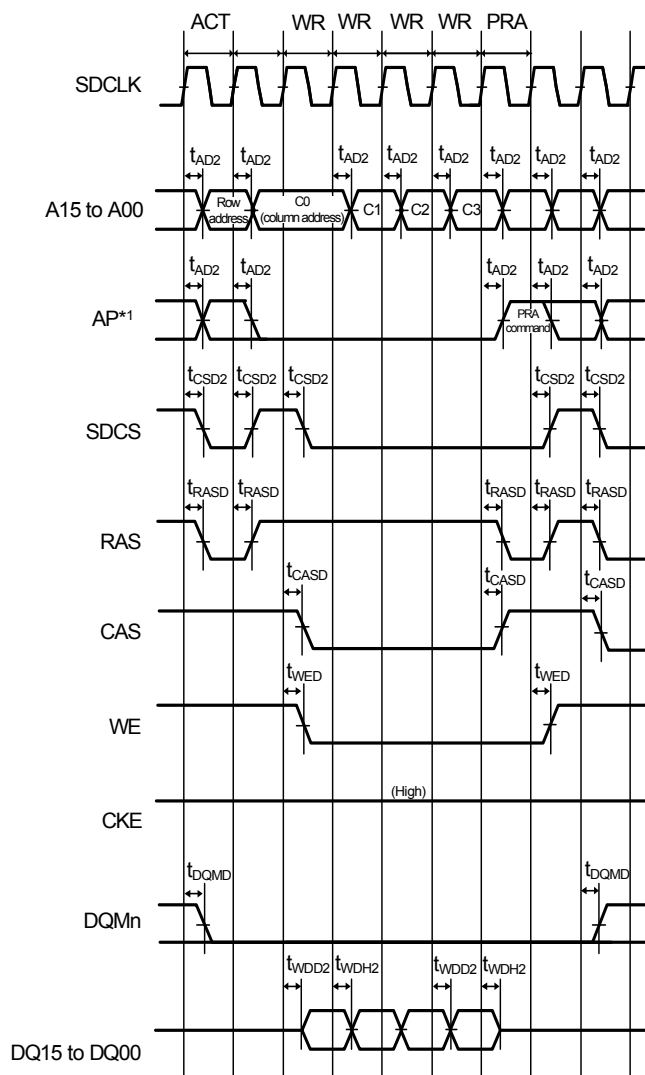


Figure 2.18 External bus timing for external wait control



Note 1. Address pins are for output of the precharge-select command (Precharge-sel) for the SDRAM.

Figure 2.22 SDRAM multiple write timing

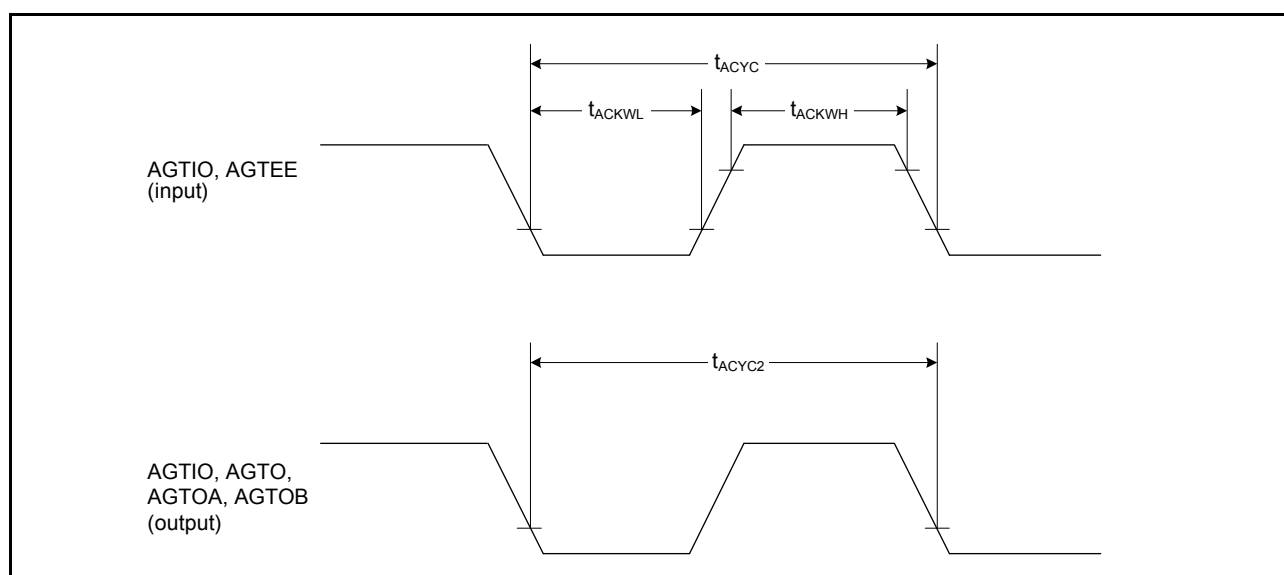


Figure 2.32 AGT input/output timing

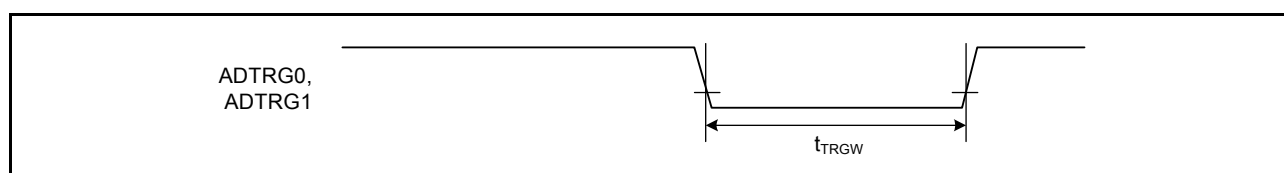


Figure 2.33 ADC12 trigger input timing

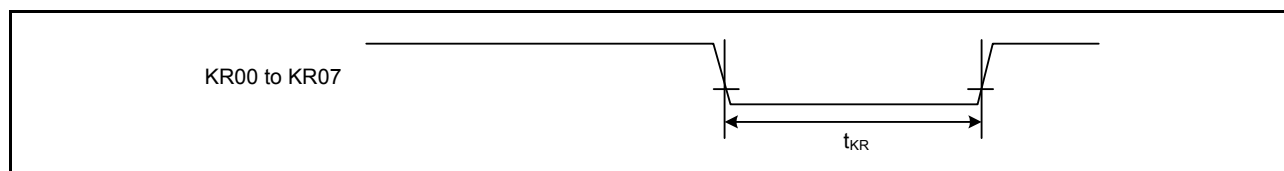


Figure 2.34 Key interrupt input timing

2.3.8 PWM Delay Generation Circuit Timing

Table 2.20 PWM Delay Generation Circuit timing

Item	Min	Typ	Max	Unit	Test conditions
Resolution	-	260	-	ps	PCLKD = 120 MHz
DNL*1	-	±2.0	-	LSB	-

Note 1. This value normalizes the differences between lines in 1-LSB resolution.

2.3.9 CAC Timing

Table 2.21 CAC timing

Item	Symbol	Min	Typ	Max	Unit	Test conditions
CAC	CACREF input pulse width	$t_{PBcyc} \leq t_{cac} \times 2$	t_{CACREF}	$4.5 \times t_{cac} + 3 \times t_{PBcyc}$	-	ns
		$t_{PBcyc} > t_{cac} \times 2$		$5 \times t_{cac} + 6.5 \times t_{PBcyc}$	-	ns

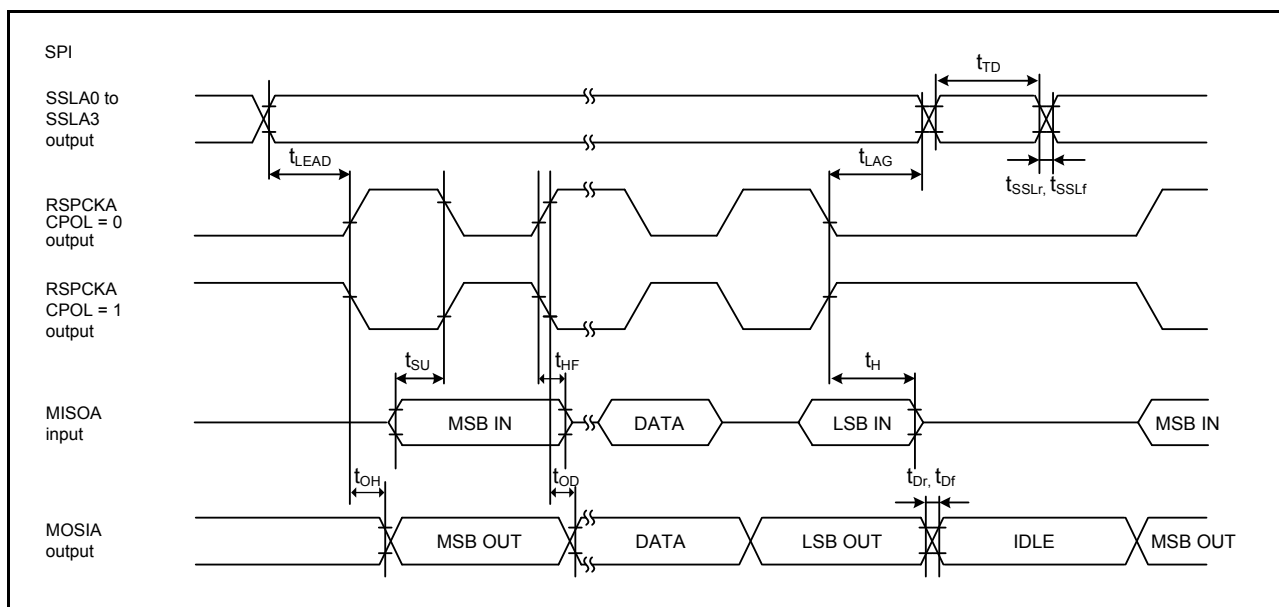


Figure 2.47 SPI timing for master when CPHA = 1 and the bit rate is set to PCLKA/2

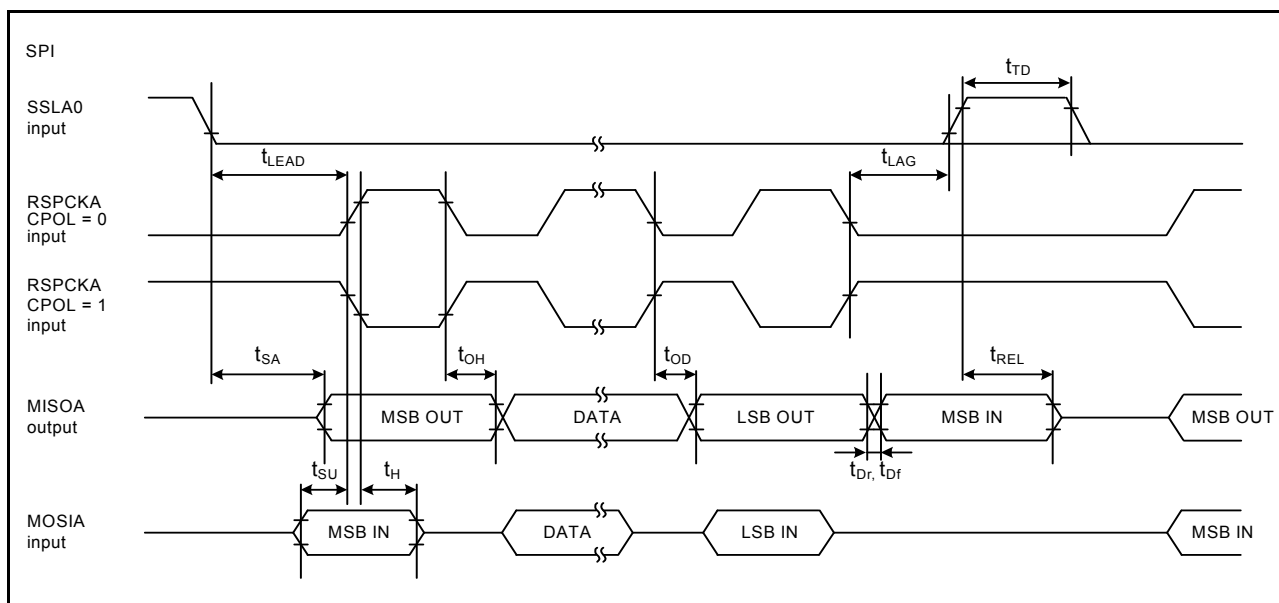


Figure 2.48 SPI timing for slave when CPHA = 0

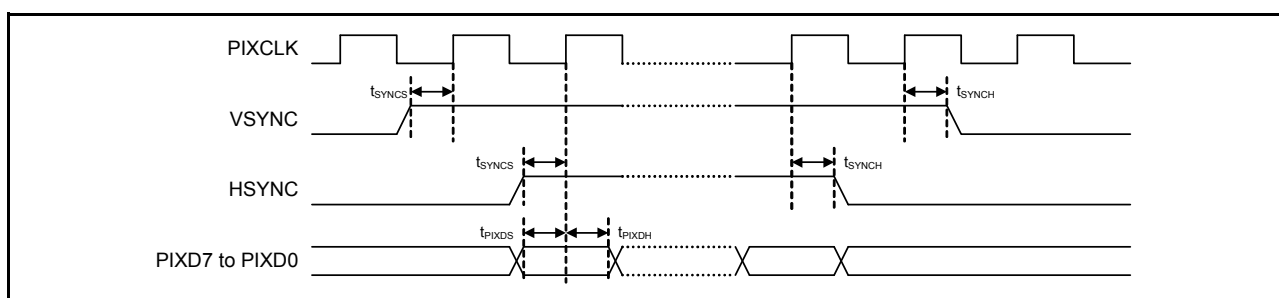


Figure 2.70 PDC AC timing

2.3.18 Graphics LCD Controller Timing

Table 2.33 Graphics LCD Controller timing

Conditions:

LCD_CLK: High drive output is selected in the port drive capability bit in the PmnPFS register.

LCD_DATA: Middle drive output is selected in the port drive capability bit in the PmnPFS register.

Item	Symbol	Min	Typ	Max	Unit	Test conditions
LCD_EXTCLK input clock frequency	$t_{E_{cyc}}$	-	-	60*1	MHz	Figure 2.71
LCD_EXTCLK input clock low pulse width	t_{WL}	0.45	-	0.55	$t_{E_{cyc}}$	
LCD_EXTCLK input clock high pulse width	t_{WH}	0.45	-	0.55	$t_{E_{cyc}}$	
LCD_CLK output clock frequency	$t_{L_{cyc}}$	-	-	60*1	MHz	Figure 2.72
LCD_CLK output clock low pulse width	t_{LOL}	0.4	-	0.6	$t_{L_{cyc}}$	Figure 2.72
LCD_CLK output clock high pulse width	t_{LOH}	0.4	-	0.6	$t_{L_{cyc}}$	Figure 2.72
LCD data output delay timing	_A or _B combinations*2	t_{DD}	-3.5	4	ns	Figure 2.73
	_A and _B combinations*3	t_{DD}	-5.0	5.5	ns	
LCD data output rise time (0.8 to 2.0 V)	t_{Dr}	-	-	2	ns	Figure 2.74
LCD data output fall time (2.0 to 0.8 V)	t_{Df}	-	-	2	ns	

Note 1. Parallel RGB888, 666,565: Maximum 54 MHz

Serial RGB888: Maximum 60 MHz (4x speed)

Note 2. Use pins that have a letter appended to their names, for instance, “_A” or “_B”, to indicate

Note 3. Pins of group “_A” and “_B” combinations are used.

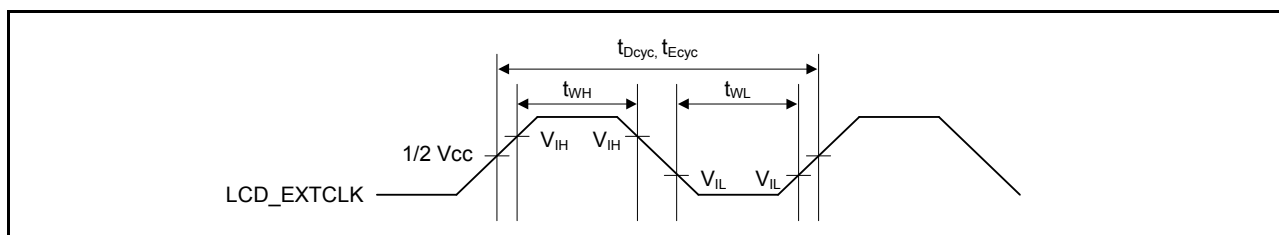


Figure 2.71 LCD_EXTCLK clock input timing

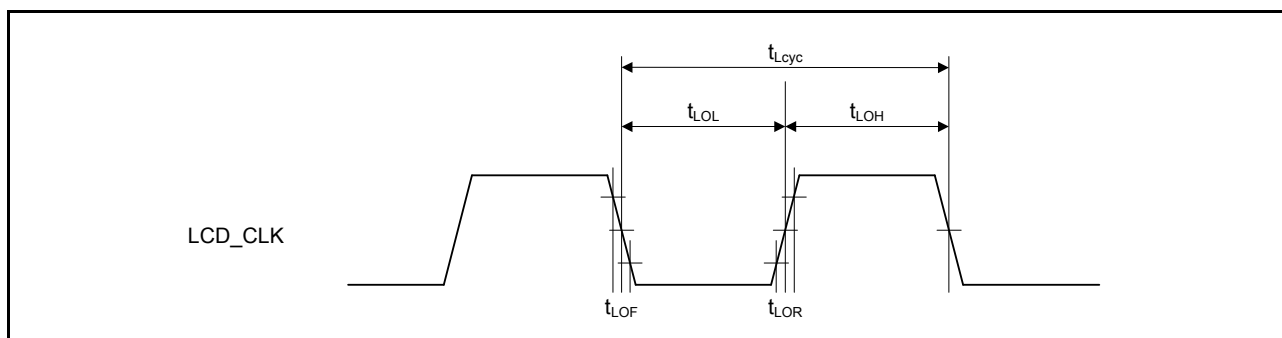


Figure 2.72 LCD_CLK clock output timing

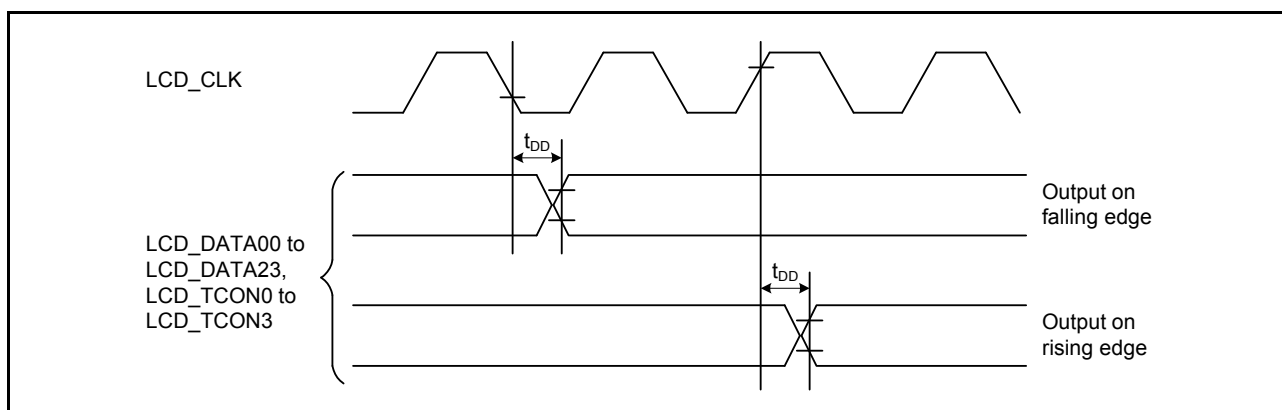


Figure 2.73 Display output timing

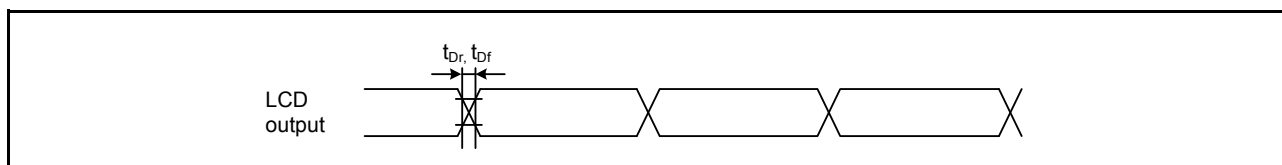


Figure 2.74 LCD output rise and fall times

2.4 USB Characteristics

2.4.1 USBHS Timing

Table 2.34 USBHS low-speed characteristics for host only (USBHS_DP and USBHS_DM pin characteristics)
(1/2)

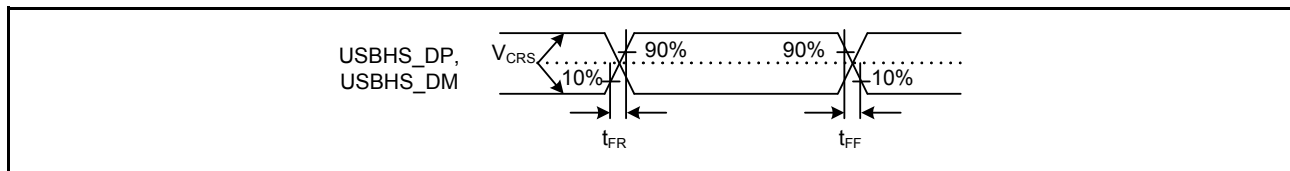
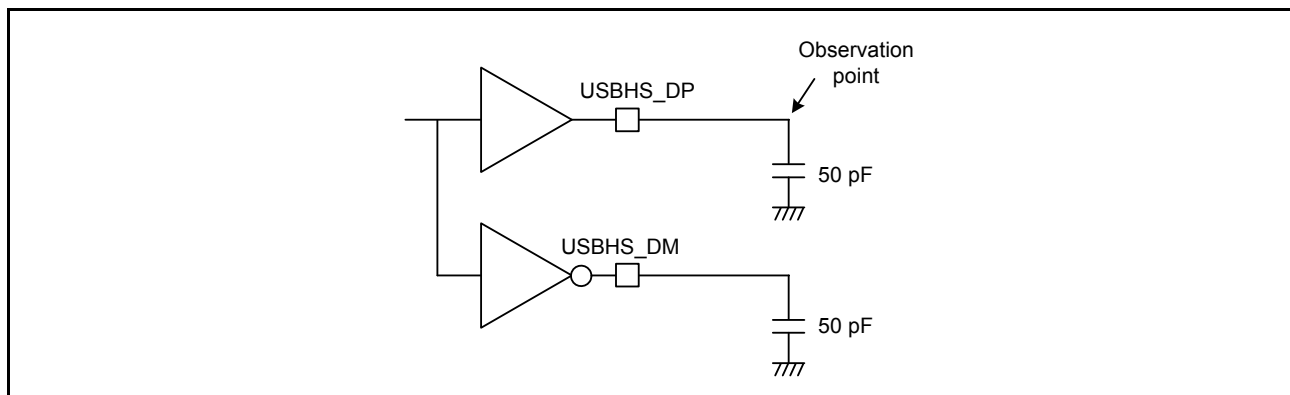
Conditions: USBHS_RREF = 2.2 kΩ ± 1%, USBMCLK = 20/24 MHz, UCLK = 48 MHz

Item		Symbol	Min	Typ	Max	Unit	Test conditions	
Input characteristics	Input high voltage	V_{IH}	2.0	-	-	V	-	-
	Input low voltage	V_{IL}	-	-	0.8	V	-	-
	Differential input sensitivity	V_{DI}	0.2	-	-	V	USBHS_DP - USBHS_DM	-
	Differential common-mode range	V_{CM}	0.8	-	2.5	V	-	-

Table 2.35 USBHS full-speed characteristics (USBHS_DP and USBHS_DM pin characteristics) (2/2)

Conditions: USBHS_RREF = 2.2 kΩ ± 1%, USBMCLK = 20/24 MHz, UCLK = 48 MHz

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Output characteristics	Output high voltage	V_{OH}	2.8	-	3.6	V	$I_{OH} = -200 \mu A$ -
	Output low voltage	V_{OL}	0.0	-	0.3	V	$I_{OL} = 2 \text{ mA}$ -
	Cross-over voltage	V_{CRS}	1.3	-	2.0	V	-
	Rise time	t_{LR}	4	-	20	ns	-
	Fall time	t_{LF}	4	-	20	ns	-
	Rise/fall time ratio	t_{LR} / t_{LF}	90	-	111.11	%	t_{FR} / t_{FF} -
	Output resistance	Z_{DRV}	40.5	-	49.5	Ω	Rs Not used (PHYSET.REPSEL[1:0] = 01b and PHYSET.HSEB = 0)
DC characteristics	USBHS_DM pull-up resistor (device)	R_{pu}	0.900	-	1.575	kΩ	During idle state
			1.425	-	3.090	kΩ	During transmission and reception
	USBHS_DP/USBHS_DM pull-down resistor (host)	R_{pd}	14.25	-	24.80	kΩ	-

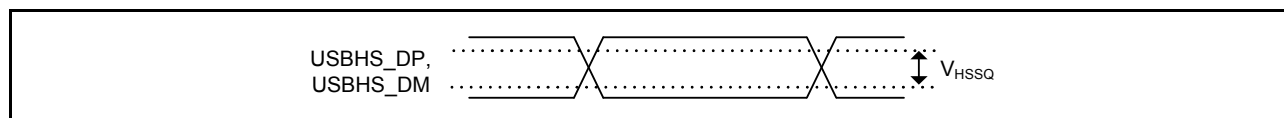
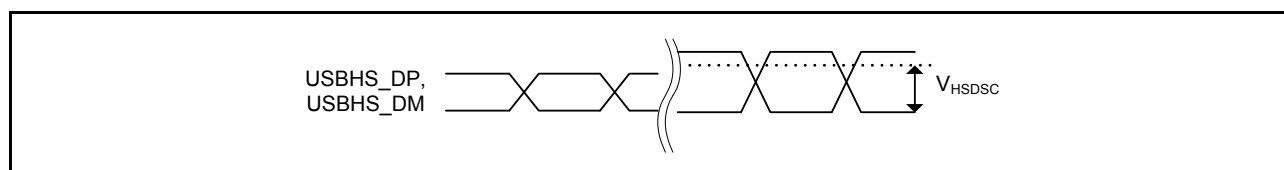
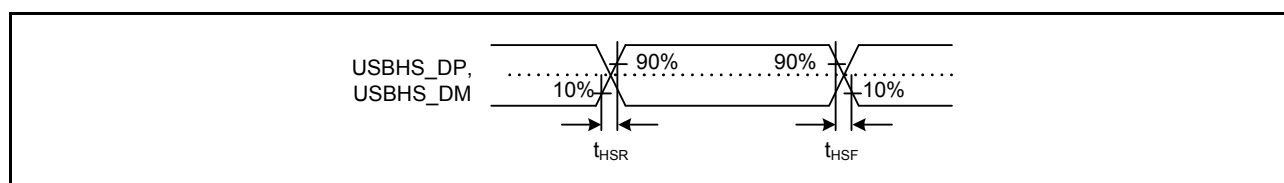
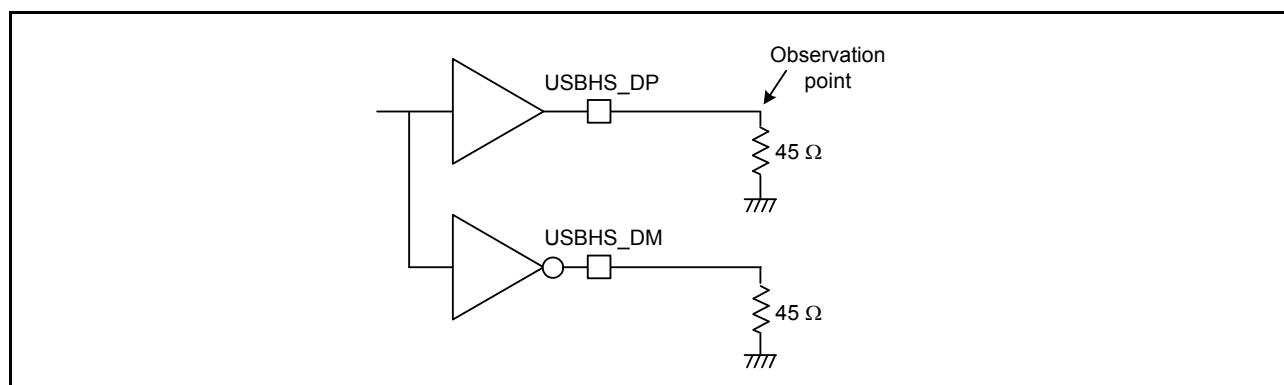
**Figure 2.77 USBHS_DP and USBHS_DM output timing in full-speed mode****Figure 2.78 Test circuit in full-speed mode****Table 2.36 USBHS high-speed characteristics (USBHS_DP and USBHS_DM pin characteristics) (1/2)**

Conditions: USBHS_RREF = 2.2 kΩ ± 1%, USBMCLK = 20/24 MHz

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Input characteristics	Squelch detect sensitivity	V_{HSSQ}	100	-	150	mV	Figure 2.79
	Disconnect detect sensitivity	V_{HSDSC}	525	-	625	mV	Figure 2.80
	Common-mode voltage	V_{HSCM}	-50	-	500	mV	-
Output characteristics	Idle state	V_{HSOI}	-10.0	-	10	mV	-
	Output high voltage	V_{HSOH}	360	-	440	mV	-
	Output low voltage	V_{HSOL}	-10.0	-	10	mV	-
	Chirp J output voltage (difference)	V_{CHIRPJ}	700	-	1100	mV	-
	Chirp K output voltage (difference)	V_{CHIRPK}	-900	-	-500	mV	-

Table 2.36 USBHS high-speed characteristics (USBHS_DP and USBHS_DM pin characteristics) (2/2)Conditions: USBHS_RREF = 2.2 k Ω \pm 1%, USBMCLK = 20/24 MHz

Item		Symbol	Min	Typ	Max	Unit	Test conditions
AC characteristics	Rise time	t_{HSR}	500	-	-	ps	Figure 2.81
	Fall time	t_{HSF}	500	-	-	ps	
	Output resistance	Z_{HSDRV}	40.5	-	49.5	Ω	-

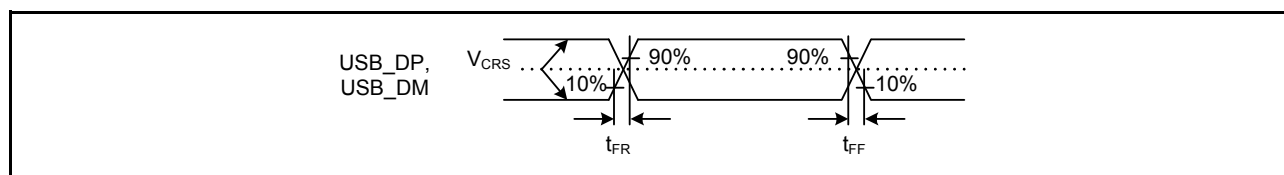
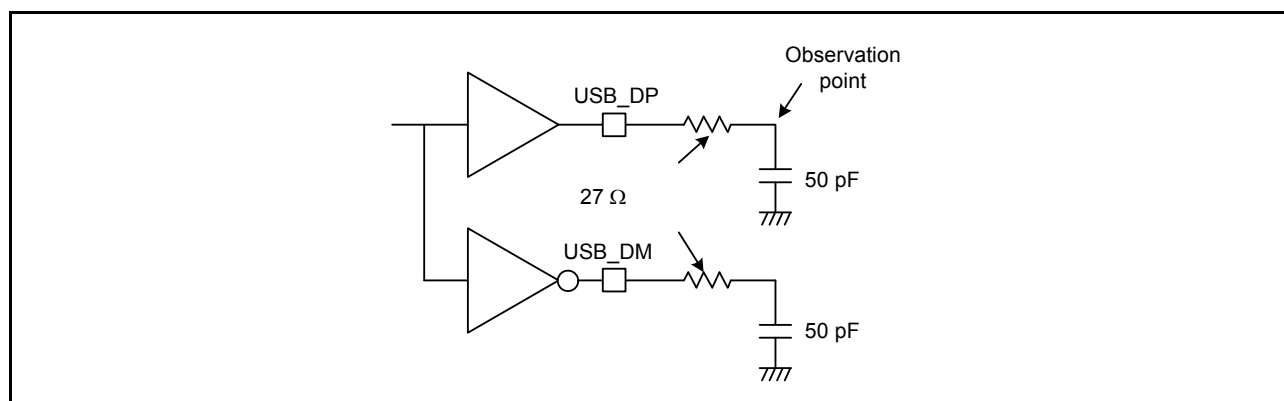
**Figure 2.79 USBHS_DP and USBHS_DM squelch detect sensitivity in high-speed mode****Figure 2.80 USBHS_DP and USBHS_DM disconnect detect sensitivity in high-speed mode****Figure 2.81 USBHS_DP and USBHS_DM output timing in high-speed mode****Figure 2.82 Test circuit in high-speed mode****Table 2.37 USBHS high-speed characteristics (USBHS_DP and USBHS_DM pin characteristics)**Conditions: USBHS_RREF = 2.2 k Ω \pm 1%, USBMCLK = 20/24 MHz

Item		Symbol	Min	Max	Unit	Test conditions
Battery Charging Specification	D+ sink current	I_{DP_SINK}	25	175	μA	-
	D- sink current	I_{DM_SINK}	25	175	μA	-
	DCD source current	I_{DP_SRC}	7	13	μA	-
	Data detection voltage	V_{DAT_REF}	0.25	0.4	V	-
	D+ source voltage	V_{DP_SRC}	0.5	0.7	V	Output current = 250 μA
	D- source voltage	V_{DM_SRC}	0.5	0.7	V	Output current = 250 μA

Table 2.39 USBFS full-speed characteristics (USB_DP and USB_DM pin characteristics) (2/2)

Conditions: $V_{CC} = AV_{CC0} = V_{CC_USB} = V_{BATT} = 3.0$ to 3.6 V, $2.7 \leq V_{REFH0}/V_{REFH} \leq AV_{CC0}$, $V_{CC_USBHS} = AV_{CC_USBHS} = 3.0$ to 3.6 V, $USBA_RREF = 2.2$ k $\Omega \pm 1\%$, $USBMCLK = 20/24$ MHz, $UCLK = 48$ MHz

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Output characteristics	Output high voltage	V_{OH}	2.8	-	3.6	V	$I_{OH} = -200$ μ A
	Output low voltage	V_{OL}	0.0	-	0.3	V	$I_{OL} = 2$ mA
	Cross-over voltage	V_{CRS}	1.3	-	2.0	V	Figure 2.85
	Rise time	t_{LR}	4	-	20	ns	
	Fall time	t_{LF}	4	-	20	ns	
	Rise/fall time ratio	t_{LR} / t_{LF}	90	-	111.11	%	t_{FR} / t_{FF}
	Output resistance	Z_{DRV}	28	-	44	Ω	USBFS: $R_s = 27$ Ω included
Pull-up and pull-down characteristics	DM pull-up resistance in device controller mode	R_{pu}	0.900	-	1.575	k Ω	During idle state
			1.425	-	3.090	k Ω	During transmission and reception
	USB_DP and USB_DM pull-down resistance in host controller mode	R_{pd}	14.25	-	24.80	k Ω	-

**Figure 2.85 USB_DP and USB_DM output timing in full-speed mode****Figure 2.86 Test circuit in full-speed mode**

2.5 ADC12 Characteristics

[Normal-precision channel]

Table 2.40 A/D conversion characteristics for unit 0 (1/2)

Conditions: $PCLKC = 1$ to 60 MHz

Item	Min	Typ	Max	Unit	Test conditions
Frequency	1	-	60	MHz	-
Analog input capacitance	-	-	30	pF	-
Quantization error	-	± 0.5	-	LSB	-
Resolution	-	-	12	Bits	-

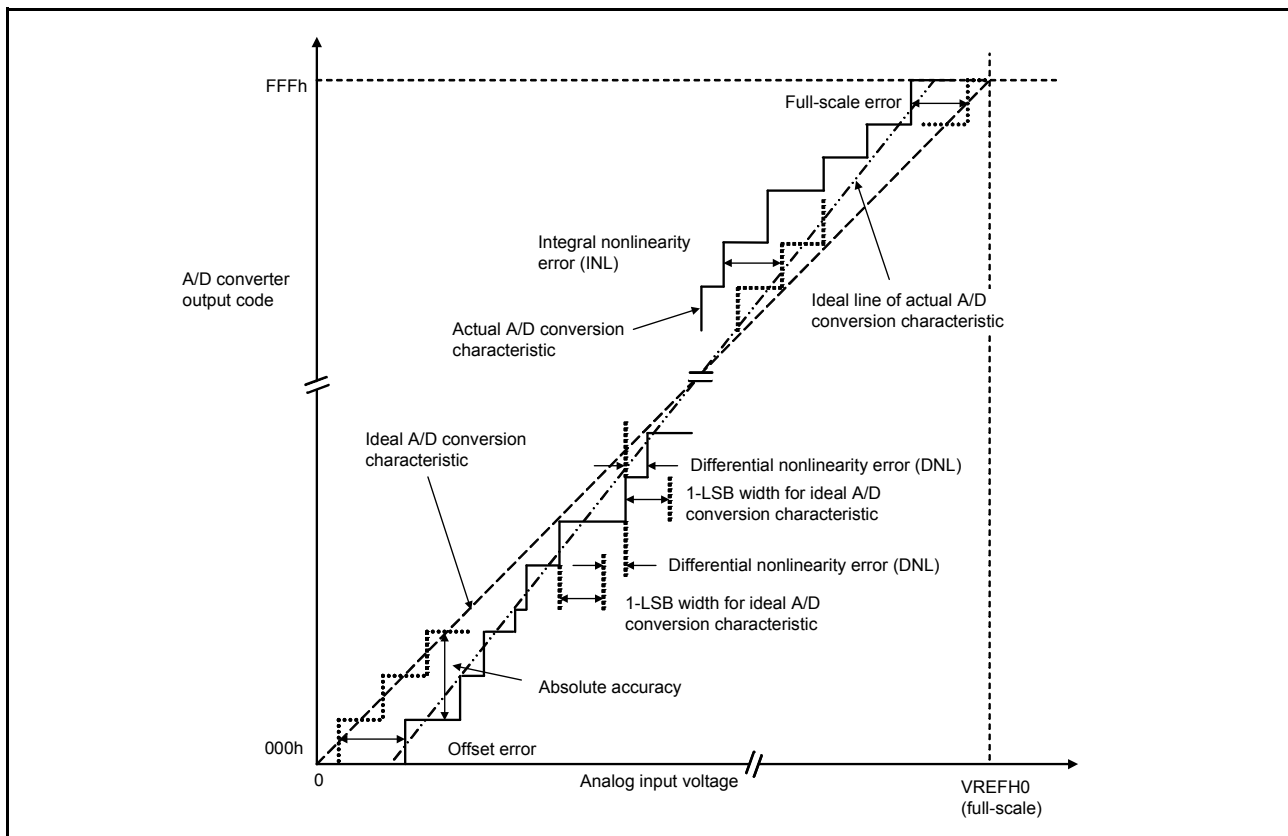


Figure 2.87 Illustration of ADC12 characteristic terms

Absolute accuracy

Absolute accuracy is the difference between output code based on the theoretical A/D conversion characteristics, and the actual A/D conversion result. When measuring absolute accuracy, the voltage at the midpoint of the width of the analog input voltage (1-LSB width), which can meet the expectation of outputting an equal code based on the theoretical A/D conversion characteristics, is used as an analog input voltage. For example, if 12-bit resolution is used and the reference voltage $V_{REFH0} = 3.072\text{ V}$, then 1-LSB width becomes 0.75 mV, and 0 mV, 0.75 mV, and 1.5 mV are used as the analog input voltages. If the analog input voltage is 6 mV, an absolute accuracy of $\pm 5\text{ LSB}$ means that the actual A/D conversion result is in the range of 003h to 00Dh, though an output code of 008h can be expected from the theoretical A/D conversion characteristics.

Integral nonlinearity error (INL)

Integral nonlinearity error is the maximum deviation between the ideal line when the measured offset and full-scale errors are zeroed, and the actual output code.

Differential nonlinearity error (DNL)

Differential nonlinearity error is the difference between the 1-LSB width based on the ideal A/D conversion characteristics and the width of the actual output code.

Offset error

Offset error is the difference between the transition point of the ideal first output code and the actual first output code.

Full-scale error

Full-scale error is the difference between the transition point of the ideal last output code and the actual last output code.

Table 2.52 Code flash memory characteristics (2/2)

Conditions: Program or erase: FCLK = 4 to 60 MHz

Read: FCLK ≤ 60 MHz

Item		Symbol	FCLK = 4 MHz			20 MHz ≤ FCLK ≤ 60 MHz			Unit
			Min	Typ	Max	Min	Typ	Max	
Erasure time $N_{PEC} > 100$ times	8-KB	t_{E8K}	-	85	260	-	47	144	ms
	32-KB	t_{E32K}	-	304	1040	-	169	576	ms
Reprogramming/erase cycle*1		N_{PEC}	1000*2	-	-	1000*2	-	-	Times
Suspend delay during programming		t_{SPD}	-	-	264	-	-	120	μs
First suspend delay during erasure in suspend priority mode		t_{SESD1}	-	-	216	-	-	120	μs
Second suspend delay during erasure in suspend priority mode		t_{SESD2}	-	-	1.7	-	-	1.7	ms
Suspend delay during erasure in erasure priority mode		t_{SEED}	-	-	1.7	-	-	1.7	ms
Forced stop command		t_{FD}	-	-	32	-	-	20	μs
Data hold time*3		t_{DRP}	20	-	-	20	-	-	Years
FCU reset time		t_{FCUR}	35	-	-	35	-	-	μs

Note 1. The reprogram/erase cycle is the number of erasures for each block. When the reprogram/erase cycle is n times ($n = 1,000$), erasing can be performed n times for each block. For example, when 256-byte programming is performed 32 times for different addresses in 8-KB blocks, and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address several times as one erasure is not enabled. (Overwriting is prohibited.)

Note 2. This is the minimum number of times to guarantee all the characteristics after reprogramming. The guaranteed range is from 1 to the minimum value.

Note 3. This indicates the characteristics when reprogramming is performed within the specified range, including the minimum value.

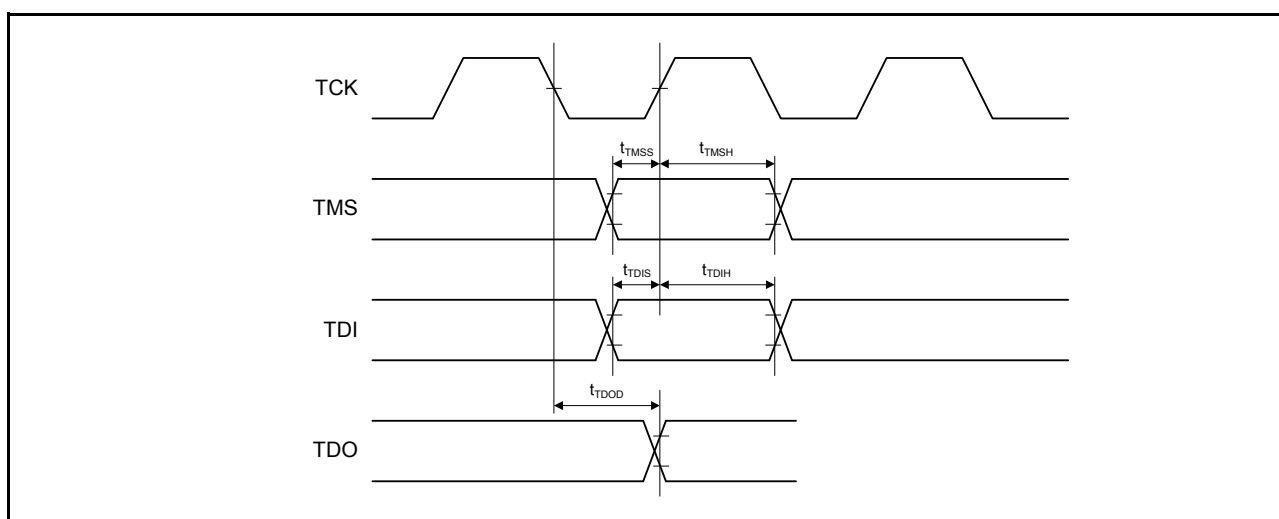


Figure 2.96 Boundary scan input/output timing

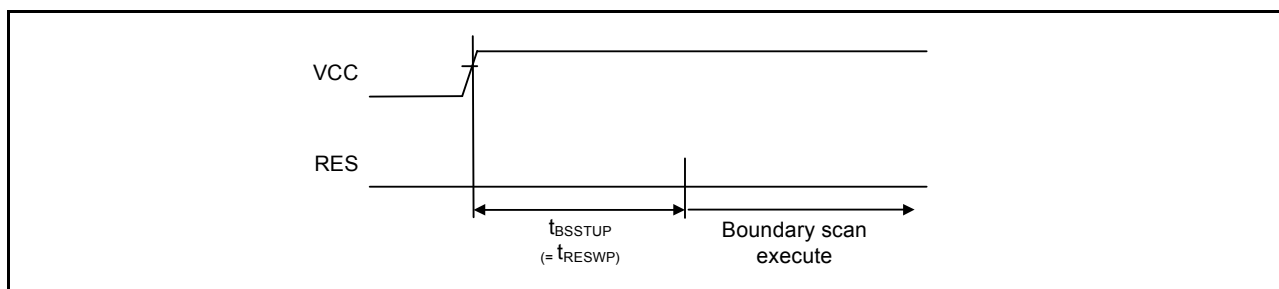


Figure 2.97 Boundary scan circuit startup timing

2.16 Joint European Test Action Group (JTAG)

Table 2.55 JTAG

Item	Symbol	Min	Typ	Max	Unit	Test conditions
TCK clock cycle time	t_{TCKcyc}	40	-	-	ns	Figure 2.95
TCK clock high pulse width	t_{TCKH}	15	-	-	ns	
TCK clock low pulse width	t_{TCKL}	15	-	-	ns	
TCK clock rise time	t_{TCKr}	-	-	5	ns	
TCK clock fall time	t_{TCKf}	-	-	5	ns	
TMS setup time	t_{TMSS}	8	-	-	ns	Figure 2.96
TMS hold time	t_{TMSH}	8	-	-	ns	
TDI setup time	t_{TDIS}	8	-	-	ns	
TDI hold time	t_{TDIH}	8	-	-	ns	
TDO data delay time	t_{TDOD}	-	-	28	ns	

Revision History	S7G2 Datasheet
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Rev.	Date	Chapter	Summary
0.80	Oct. 12, 2015	—	First Edition issued
0.85	Dec. 15, 2015	—	Second Edition issued
1.00	Feb. 23, 2016	section 1, Overview	Updated VREFH and VREFL descriptions in Table 1.16, Pin functions
		section 2, Electrical Characteristics	Updated operating and standby current information in section 2.2.5, Operating and Standby Current
			Added section 2.16, Joint European Test Action Group (JTAG)
			Added section 2.17, Serial Wire Debug (SWD)
			Added section 2.18, Embedded Trace Macro Interface (ETM)
			Updated Table 2.13, Clock timing except for sub-clock oscillator
			Updated SPI data in Table 2.25, SPI timing
			Updated Table 2.40, A/D conversion characteristics for unit 0
			Updated Table 2.41, A/D conversion characteristics for unit 1
			Updated SPI data in Figure 2.45, SPI timing for master when CPHA = 0 and the bit rate is set to PCLKA/2
			Updated Table 2.5, I/O IOH, IOL
		All	Deleted # from pin names

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